

[METHOD OF FABRICATING FLASH MEMORY]

Abstract

A method of fabricating a flash memory. A tunneling dielectric layer, a conductive layer and a mask layer are sequentially formed on a substrate. The mask layer, the conductive layer and the tunneling dielectric layer are patterned to form longitudinally arranged strips on the substrate. Buried drain regions are then formed in the substrate between the strips. The strips are further patterned into floating gate structures. An insulation layer is formed on perimeters of the floating gate structures. The insulation layer has a top surface lower than a top surface of the conductive layer of the floating gate structures, such that a part of sidewalls of the conductive layer is exposed. The mask layer is removed, a gate dielectric layer is formed on the exposed conductive layer, and a control gate is formed on the gate dielectric layer.